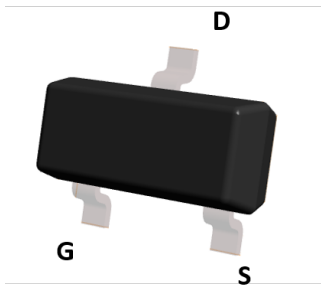
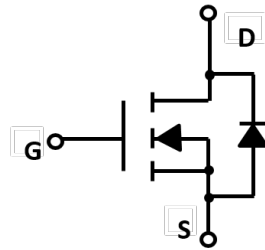
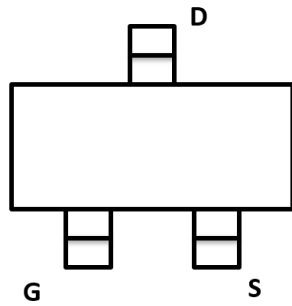


N-Channel Enhancement Mode Field Effect Transistor



Top View

SOT-23



Product Summary

- V_{DS} 60V
- I_D 340mA
- $R_{DS(ON)}$ (at $V_{GS}=10V$) < 2.5ohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) < 3.0ohm

General Description

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	60	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^\circ\text{C}$ @ Steady State	340
		$T_A=70^\circ\text{C}$ @ Steady State	272
Pulsed Drain Current ^A	I_{DM}	1.5	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	350	mW
Thermal Resistance Junction-to-Ambient @ Steady State ^B	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
2N7002	F2	7002.	3000	30000	120000	7" reel



2N7002

■ Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS1}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
	I_{GSS2}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 50	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=300mA$		1.2	2.5	Ω
		$V_{GS}=4.5V, I_D=200mA$		1.3	3.0	
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=200mA$	80			ms
Diode Forward Voltage	V_{SD}	$I_S=300mA, V_{GS}=0V$			1.2	V
Maximum Body-Diode Continuous Current	I_S				340	mA
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V, f=1MHz$		27.5		pF
Output Capacitance	C_{oss}			2.75		
Reverse Transfer Capacitance	C_{rss}			1.9		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=30V, I_D=0.3A$		1.6		nC
Gate-Source Charge	Q_{gs}			0.47		
Gate-Drain Charge	Q_{gd}			0.25		
Reverse Recovery Charge	Q_{rr}	$I_F=0.3A, di/dt=-100A/us$		2.5		ns
Reverse Recovery Time	t_{rr}			11.5		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=30V, I_D=300mA, R_{GEN}=6\Omega$		3.3		ns
Turn-on Rise Time	t_r			19		
Turn-off Delay Time	$t_{D(off)}$			9.6		
Turn-off fall Time	t_f			49		

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

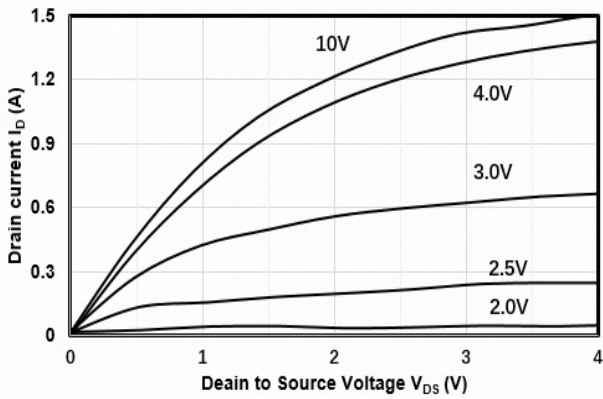


Figure1. Output Characteristics

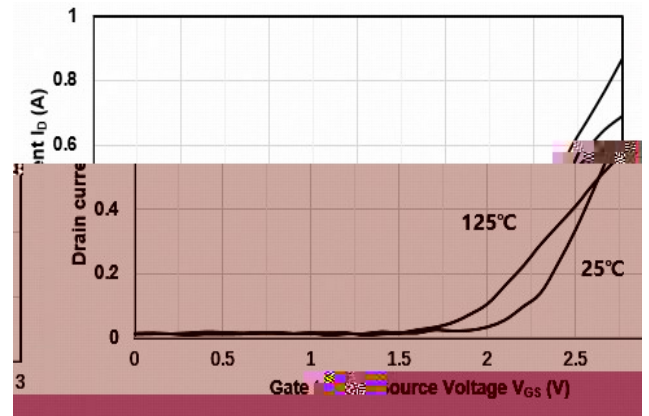


Figure2. Transfer Characteristics

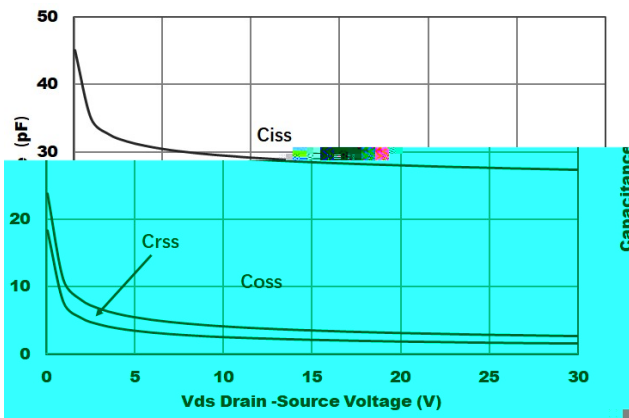


Figure3. Capacitance Characteristics

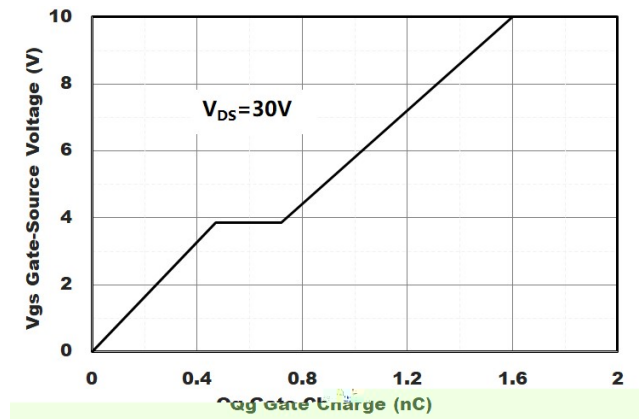


Figure4. Gate Charge

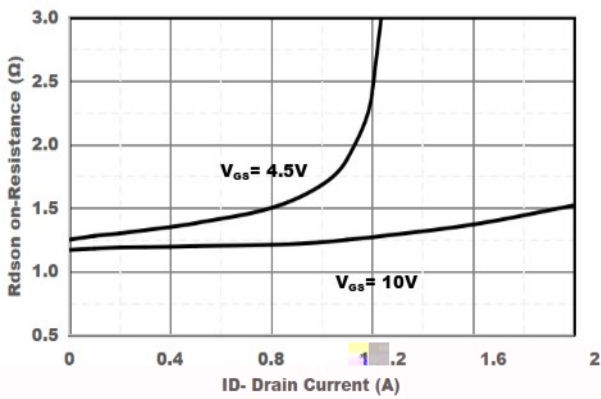


Figure5. Drain-Source on Resistance

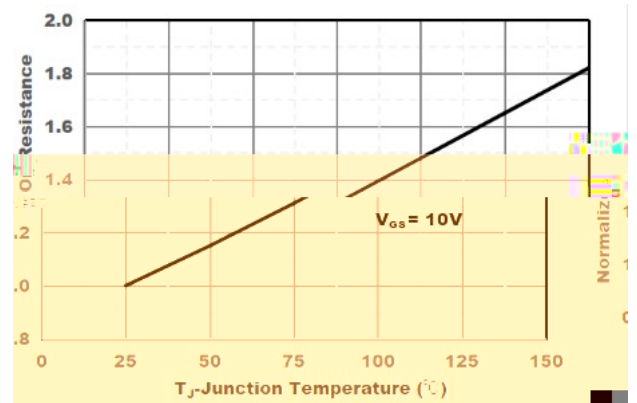


Figure6. Drain-Source on Resistance

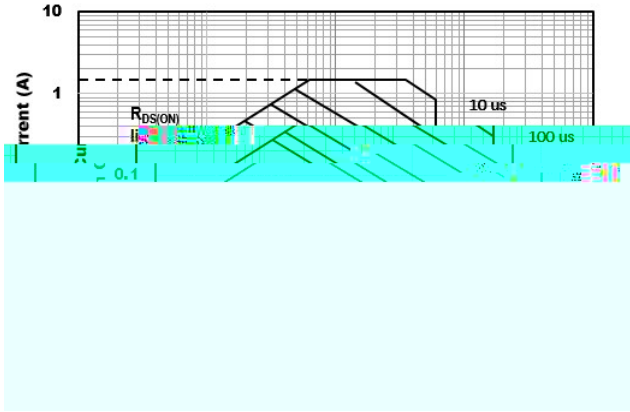


Figure7. Safe Operation Area

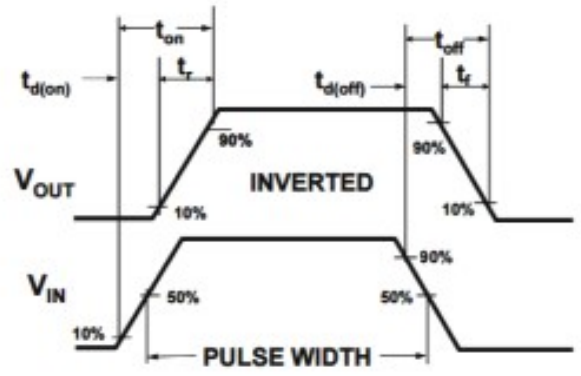
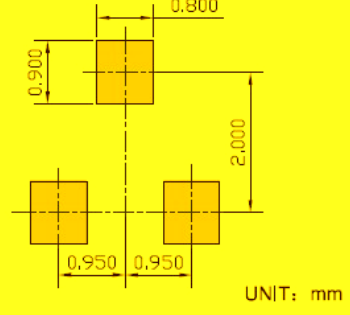
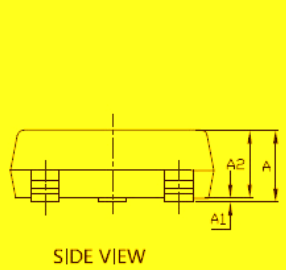
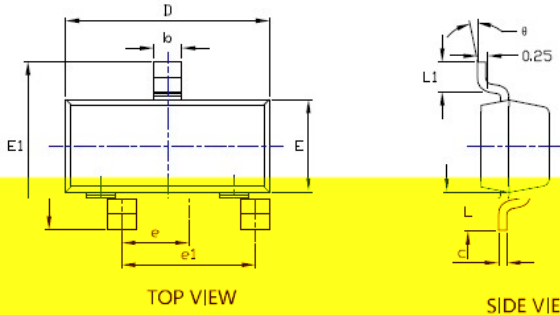


Figure8. Switching wave

■ SOT-23 Package information



SYMBOL	DIMENSIONS					
	INCHES		MILLIMETERS			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.035	---	0.045	0.900	---	1.150
A1	0.000	---	0.004	0.000	---	0.100
A2	0.035	0.038	0.041	0.900	0.975	1.050
b	0.012	0.016	0.020	0.300	0.400	0.500
c	0.004	---	0.008	0.100	---	0.200
D	0.110	0.114	0.118	2.800	2.900	3.000
E	0.047	0.051	0.055	1.200	1.300	1.400
E1	0.089	0.094	0.100	2.250	2.400	2.550
e	0.037TYP			0.950TYP		
e1	0.071	0.075	0.079	1.800	1.900	2.000
L	0.022REF			0.550REF		
L1	0.012	0.016	0.200	0.300	0.400	0.500
ø	0*	---	8*	0*	---	8*

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS,
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



2N7002

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website [http:// www.21yangjie.com](http://www.21yangjie.com) , or consult your nearest Yangjie's sales office for further assistance.